

### General Description

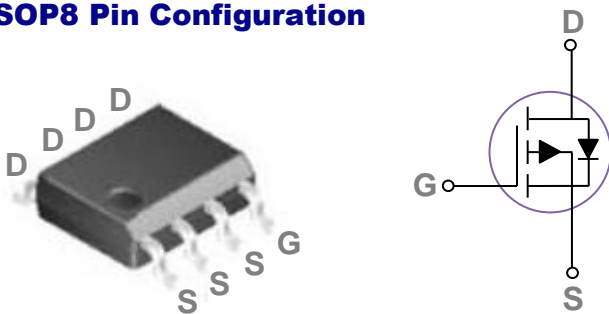
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-30V	10.8mΩ	-10A

### Features

- -30V,-10A,  $R_{DS(ON)} = 10.8m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

### SOP8 Pin Configuration



### Applications

- MB / VGA / Vcore
- POL Applications
- Load Switch
- LED Application

### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_A=25^\circ\text{C}$ )	-10	A
	Drain Current – Continuous ( $T_A=70^\circ\text{C}$ )	-8	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-40	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	125	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	50	A
$P_D$	Power Dissipation ( $T_A=25^\circ\text{C}$ )	2	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.016	W/°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A	---	9	10.8	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A	---	14	18	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	-1.6	-2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A	---	11	---	S

**Dynamic and switching Characteristics**

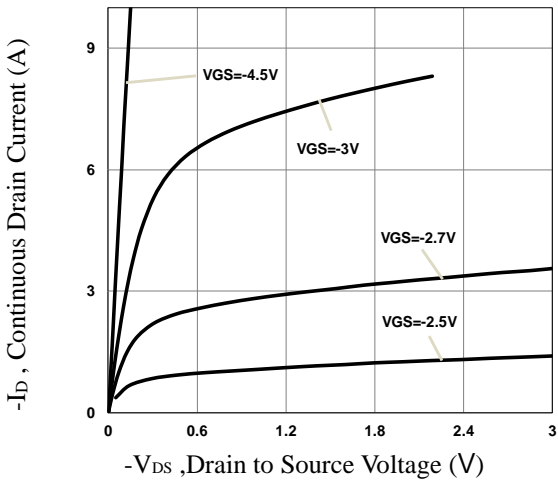
Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A	---	34	50	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	5.2	7.8	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	7.9	12	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω I <sub>D</sub> =-5A	---	20	30	ns
T <sub>r</sub>	Rise Time <sup>3, 4</sup>		---	15	22	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	40	60	
T <sub>f</sub>	Fall Time <sup>3, 4</sup>		---	30	45	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1MHz	---	2020	3000	pF
C <sub>oss</sub>	Output Capacitance		---	305	460	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	245	370	

**Drain-Source Diode Characteristics and Maximum Ratings**

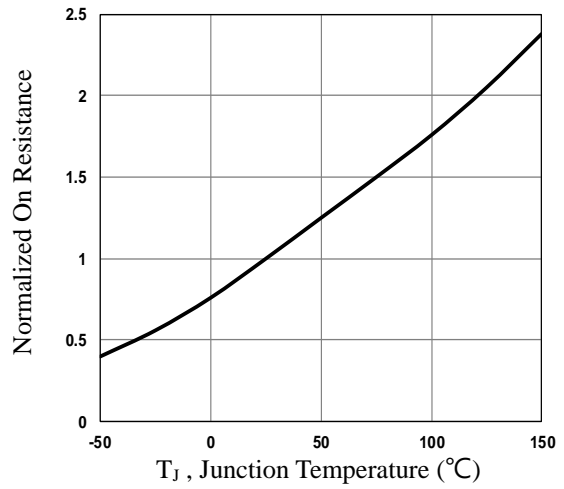
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-10	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-20	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>R</sub> =-30V, I <sub>R</sub> =-10A	---	80	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs, T <sub>J</sub> =25°C	---	170	---	nC

Note :

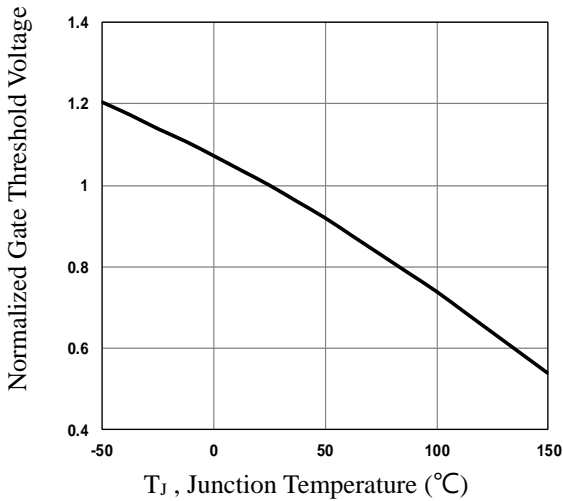
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=50A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



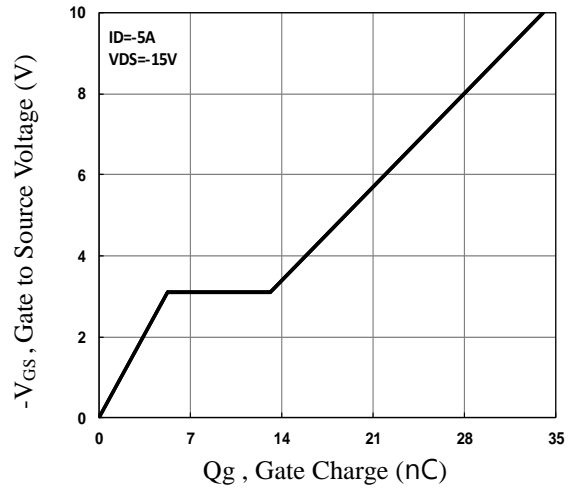
**Fig.1 Typical Output Characteristics**



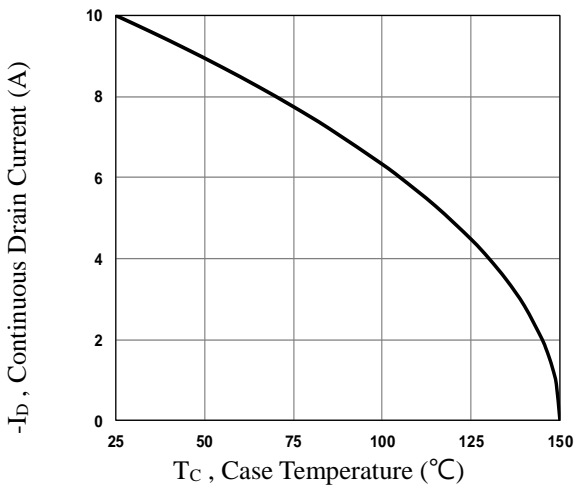
**Fig.2 Normalized RDS(on) vs. TJ**



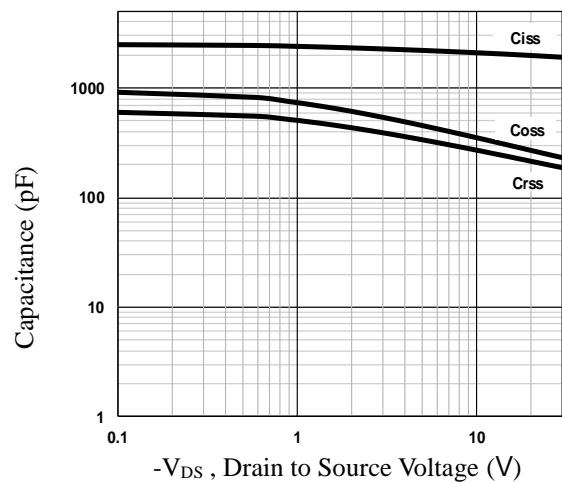
**Fig.3 Normalized V<sub>th</sub> vs. TJ**



**Fig.4 Gate Charge Waveform**



**Fig.5 Continuous Drain Current vs. TC**



**Fig.6 Capacitance Characteristics**

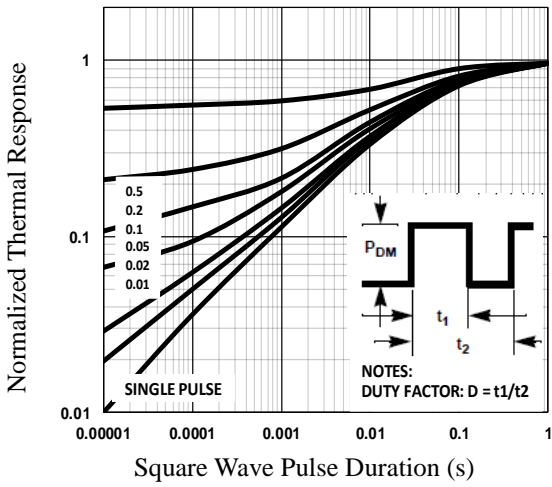


Fig.7 Normalized Transient Impedance

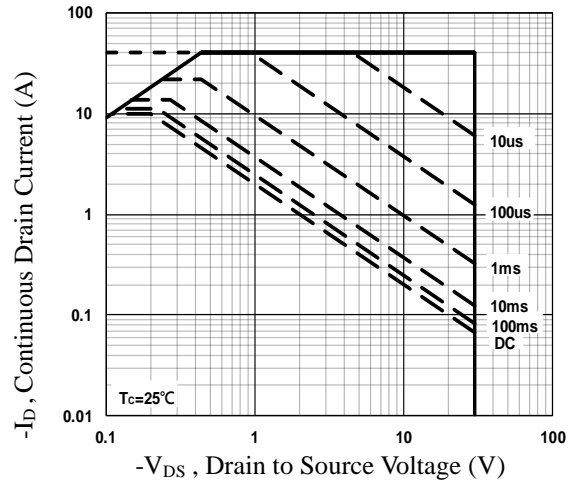


Fig.8 Maximum Safe Operation Area

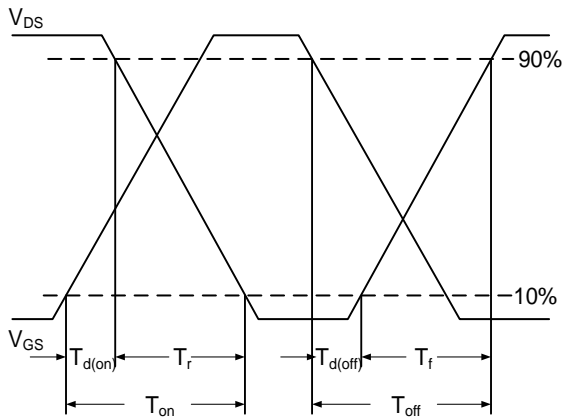


Fig.9 Switching Time Waveform

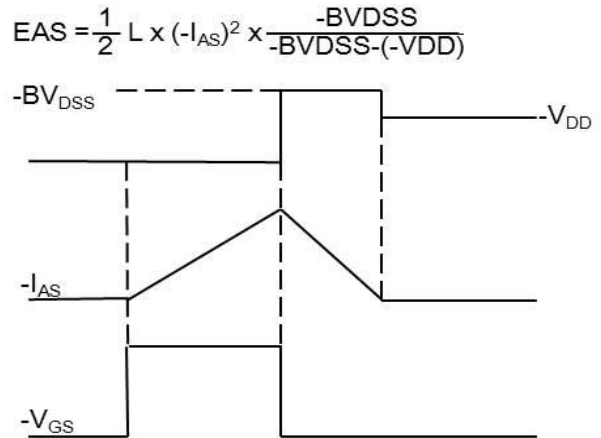
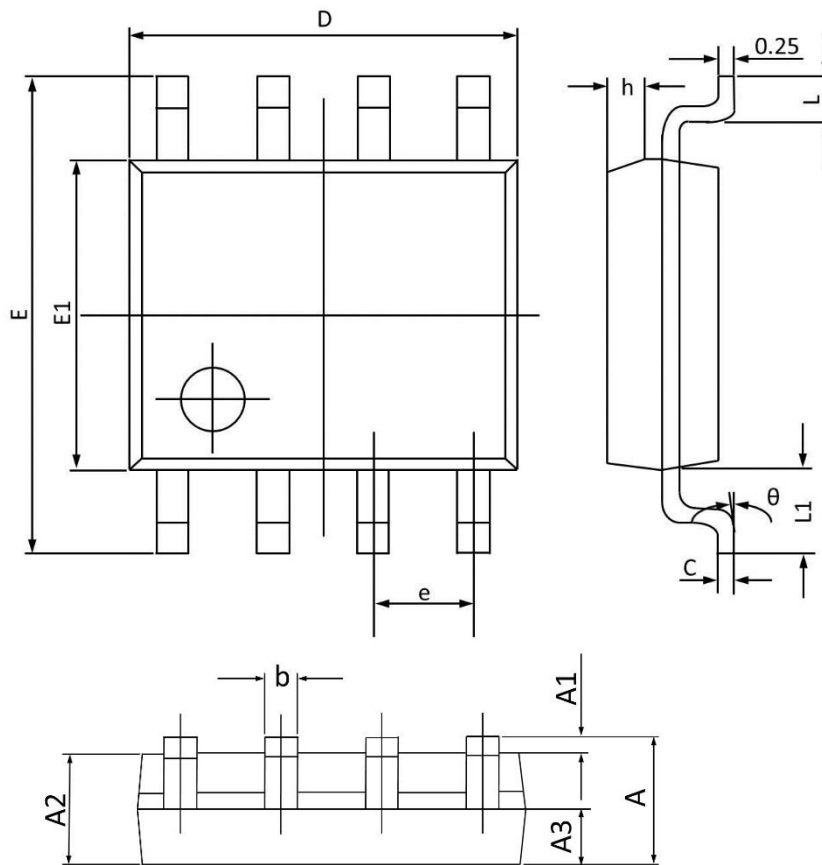


Fig.10 EAS Waveform

## SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.800	0.053	0.069
A1	0.050	0.250	0.002	0.010
A2	1.250	1.650	0.049	0.065
A3	0.500	0.700	0.020	0.028
b	0.300	0.510	0.012	0.020
c	0.150	0.260	0.006	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.020
L	0.400	1.000	0.016	0.039
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°